

LM136-2.5-N, LM236-2.5-N, LM336-2.5-NV Reference Diode

Check for Samples: LM136-2.5-N

FEATURES

- Low Temperature Coefficient
- Wide Operating Current of 400 µA to 10 mA
- 0.2Ω Dynamic Impedance
- ±1% Initial Tolerance Available
- Specified Temperature Stability
- Easily Trimmed for Minimum Temperature Drift
- Fast Turn-On

DESCRIPTION

The LM136-2.5-N/LM236-2.5-N and LM336-2.5-N integrated circuits are precision 2.5V shunt regulator diodes. These monolithic IC voltage references operate as a low-temperature-coefficient 2.5V zener with 0.2 Ω dynamic impedance. A third terminal on the LM136-2.5-N allows the reference voltage and temperature coefficient to be trimmed easily.

Connection Diagram

The LM136-2.5-N series is useful as a precision 2.5V low voltage reference for digital voltmeters, power supplies or op amp circuitry. The 2.5V make it convenient to obtain a stable reference from 5V logic supplies. Further, since the LM136-2.5-N operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

The LM136-2.5-N is rated for operation over -55° C to +125°C while the LM236-2.5-N is rated over a -25° C to +85°C temperature range.

The LM336-2.5-N is rated for operation over a 0°C to +70°C temperature range. See the connection diagrams for available packages.

TO Metal Can Package

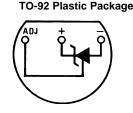


Figure 1. Bottom View See Package Number LP

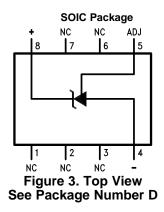


Figure 2. Bottom View See Package Number NDV

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Typical Applications

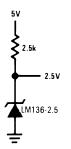
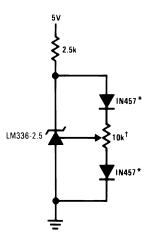


Figure 4. 2.5V Reference



[†]Adjust to 2.490V ^{*}Any silicon signal diode



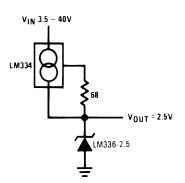


Figure 6. Wide Input Range Reference



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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Absolute Maximum Ratings⁽¹⁾⁽²⁾

Reverse Current		15 mA			
Forward Current		10 mA			
Storage Temperature		−60°C to +150°C			
Operating Temperature Range ⁽³⁾		LM136	−55°C to +150°C		
		LM236	−25°C to +85°C		
		LM336	0°C to +70°C		
Soldering Information	TO-92 Package (10 sec.))	260°C		
	TO Package (10 sec.)		300°C		
	SOIC Package	Vapor Phase (60 sec.)	215°C		
		Infrared (15 sec.)	220°C		

(1) Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Electrical specifications do not apply when operating the device beyond its specified operating conditions.

- (2) If Military/Aerospace specified devices are required, please contact the Texas Instruments Sales Office/Distributors for availability and specifications.
- (3) For elevated temperature operation, T_j max is:

LM136 150°C LM236 125°C

LM336 100°C

Thermal Resistance	TO-92	то	SOIC
θ_{ja} (Junction to Ambient)	180°C/W (0.4″ leads)	440°C/W	165°C/W
	170°C/W (0.125" lead)		
θ _{ja} (Junction to Case)	n/a	80°C/W	n/a

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Electrical Characteristics ⁽¹⁾

Parameter	c	LM136A-2.5-N/ LM236A-2.5-N LM136-2.5-N/ LM136-2.5-N/			LM336B-2.5-N LM336-2.5-N			Units	
		Min	Тур	Max	Min	Тур	Max		
Reverse	T _A =25°C, I _R =1 mA	LM136, LM236, LM336	2.440	2.490	2.540	2.390	2.490	2.590	V
Breakdown Voltage		LM136A, LM236A, LM336B	2.465	2.490	2.515	2.440	2.490	2.540	V
Reverse Breakdown Change With Current	T _A =25°C, 400 μA≤I _R ≤10 mA			2.6	6		2.6	10	mV
Reverse Dynamic Impedance	$T_A=25^{\circ}C, I_R=1 \text{ mA}, f = 10$		0.2	0.6		0.2	1	Ω	
Temperature Stability ⁽²⁾	V _R Adjusted to 2.490V	0°C≤T _A ≤70°C (LM336)					1.8	6	mV
	I _R =1 mAFigure 15	−25°C≤T _A ≤+85°C (LM236H, LM236Z)		3.5	9				mV
		$-25^{\circ}C \le T_A \le +85^{\circ}C$ (LM236M)		7.5	18				mV
		−55°C≤T _A ≤+125°C (LM136)		12	18				mV
Reverse Breakdown Change With Current	400 µA≤I _R ≤10 mA			3	10		3	12	mV
Reverse Dynamic Impedance	I _R =1 mA		0.4	1		0.4	1.4	Ω	
Long Term Stability	$T_A=25^{\circ}C \pm 0.1^{\circ}C, I_R=1 m$ t = 1000 hrs	А,		20			20		ppm

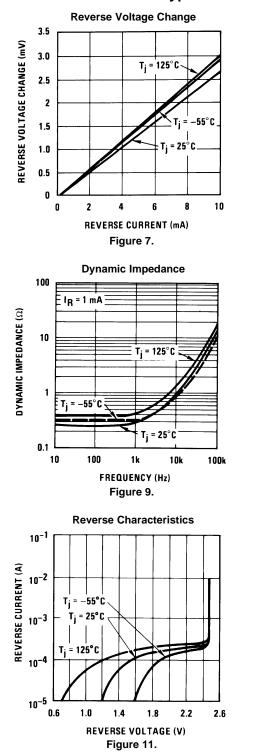
Unless otherwise specified, the LM136-2.5-N is specified from -55°C ≤ T_A ≤ +125°C, the LM236-2.5-N from -25°C ≤ T_A ≤ +85°C and the LM336-2.5-N from 0°C ≤ T_A ≤ +70°C.
 Temperature stability for the LM336 and LM236 family is specified by design. Design limits are ensured (but not 100% production

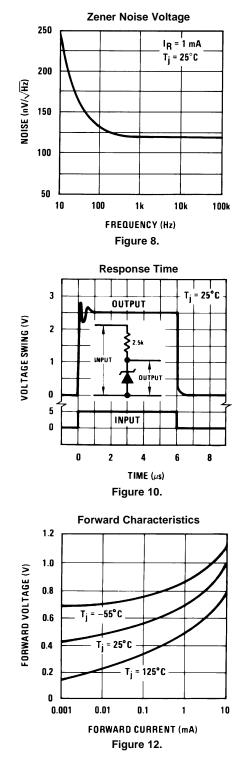
(2) Temperature stability for the LM336 and LM236 family is specified by design. Design limits are ensured (but not 100% production tested) over the indicated temperature and supply voltage ranges. These limits are not used to calculate outgoing quality levels. Stability is defined as the maximum change in V_{ref} from 25°C to T_A (min) or T_A (max).

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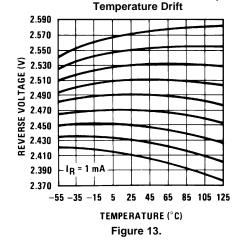


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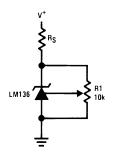


APPLICATION HINTS

The LM136 series voltage references are much easier to use than ordinary zener diodes. Their low impedance and wide operating current range simplify biasing in almost any circuit. Further, either the breakdown voltage or the temperature coefficient can be adjusted to optimize circuit performance.

Figure 14 shows an LM136 with a 10k potentiometer for adjusting the reverse breakdown voltage. With the addition of R1 the breakdown voltage can be adjusted without affecting the temperature coefficient of the device. The adjustment range is usually sufficient to adjust for both the initial device tolerance and inaccuracies in buffer circuitry.

If minimum temperature coefficient is desired, two diodes can be added in series with the adjustment potentiometer as shown in Figure 15. When the device is adjusted to 2.490V the temperature coefficient is minimized. Almost any silicon signal diode can be used for this purpose such as a 1N914, 1N4148 or a 1N457. For proper temperature compensation the diodes should be in the same thermal environment as the LM136. It is usually sufficient to mount the diodes near the LM136 on the printed circuit board. The absolute resistance of R1 is not critical and any value from 2k to 20k will work.



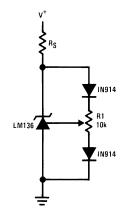


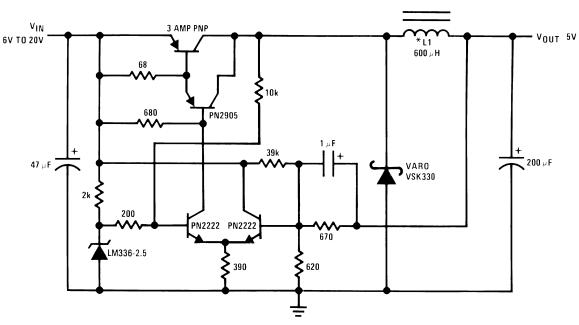
Figure 14. LM136 With Pot for Adjustment of Breakdown Voltage (Trim Range = ±120 mV typical)

Figure 15. Temperature Coefficient Adjustment (Trim Range = ±70 mV typical)

6



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^{*}L1 60 turns #16 wire on Arnold Core A-254168-2 [†]Efficiency $\approx 80\%$



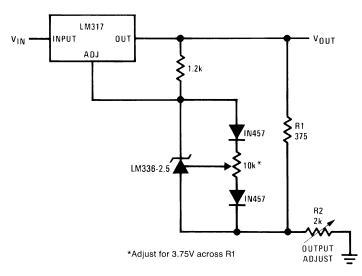
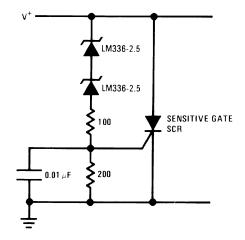


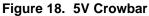
Figure 17. Precision Power Regulator with Low Temperature Coefficient

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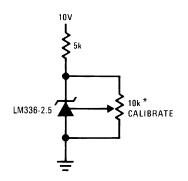




Figure 19. Trimmed 2.5V Reference with Temperature Coefficient Independent of Breakdown Voltage

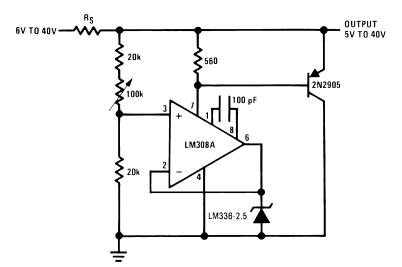
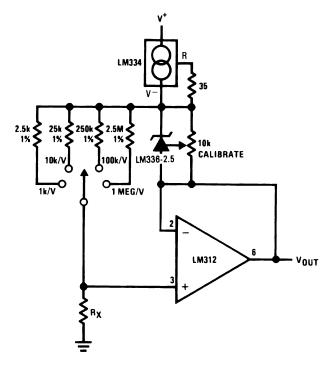


Figure 20. Adjustable Shunt Regulator

EXAS

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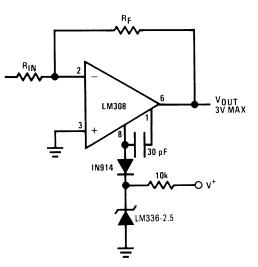


Figure 22. Op Amp with Output Clamped



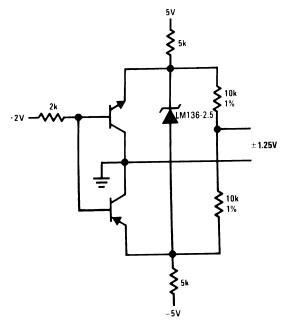
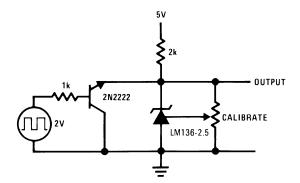


Figure 23. Bipolar Output Reference





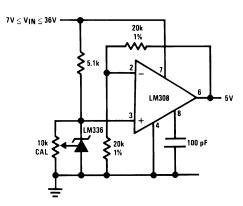


Figure 25. 5V Buffered Reference



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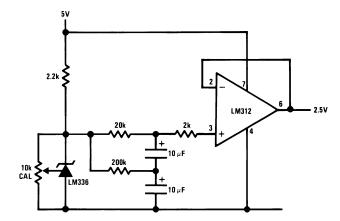
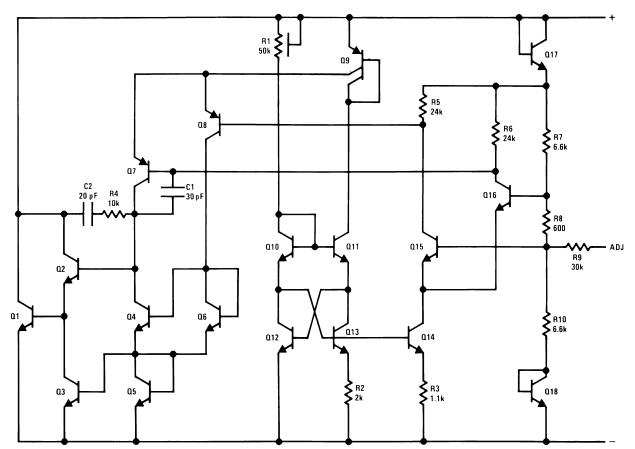


Figure 26. Low Noise Buffered Reference

Schematic Diagram



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REVISION HISTORY

Changes from Revision E (April 2013) to Revision F					
•	Changed layout of National Data Sheet to TI format	11			



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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
LM136AH-2.5	ACTIVE	то	NDV	3	1000	Non-RoHS & Non-Green	Call TI	Call TI	-40 to 125	(LM136AH2.5, LM13 6AH2.5)	Samples
LM136AH-2.5/NOPB	ACTIVE	то	NDV	3	1000	RoHS & Green	Call TI	Level-1-NA-UNLIM	-40 to 125	(LM136AH2.5, LM13 6AH2.5)	Samples
LM136H-2.5	ACTIVE	то	NDV	3	1000	Non-RoHS & Non-Green	Call TI	Call TI	-55 to 125	(LM136H2.5, LM136 H2.5)	Samples
LM136H-2.5/NOPB	ACTIVE	то	NDV	3	1000	RoHS & Green	Call TI	Level-1-NA-UNLIM	-55 to 125	(LM136H2.5, LM136 H2.5)	Samples
LM236H-2.5	ACTIVE	то	NDV	3	1000	Non-RoHS & Non-Green	Call TI	Call TI	-25 to 85	(LM236H2.5, LM236 H2.5)	Samples
LM236H-2.5/NOPB	ACTIVE	то	NDV	3	1000	RoHS & Green	Call TI	Level-1-NA-UNLIM	-25 to 85	(LM236H2.5, LM236 H2.5)	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <= 1000ppm threshold. Antimony trioxide based flame retardants must also meet the <= 1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

10-Dec-2020

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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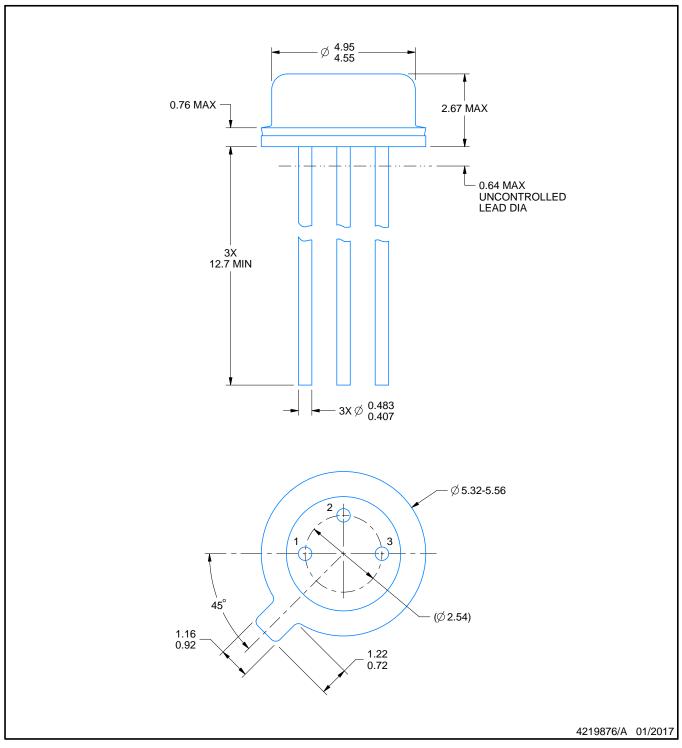
NDV0003H



PACKAGE OUTLINE

TO-CAN - 2.67 mm max height

TO-46



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC registration TO-46.

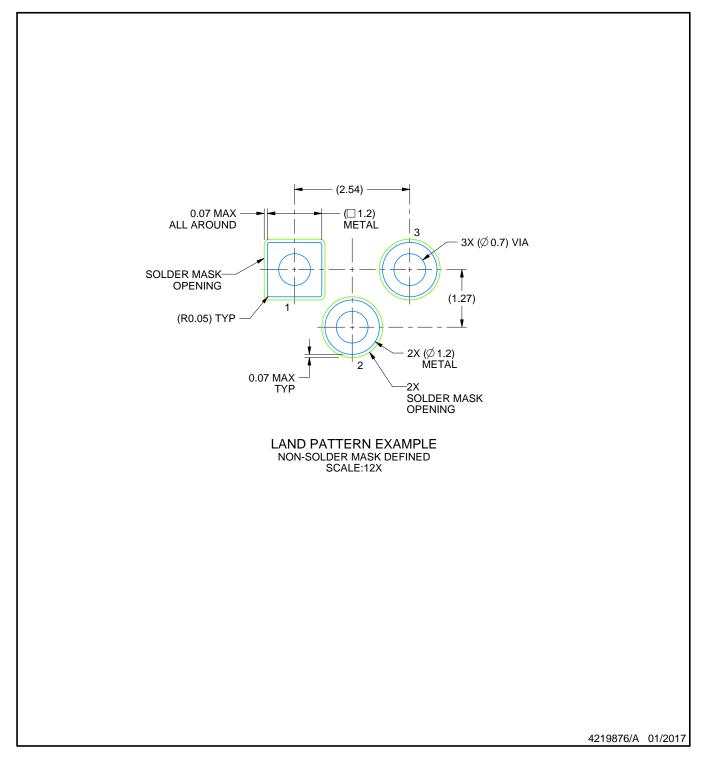


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EXAMPLE BOARD LAYOUT

TO-CAN - 2.67 mm max height

TO-46





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